

PCN# 20190627003.1 Transfer of select HV700 devices from GFAB to FFAB Wafer Fab site Change Notification / Sample Request

Date: July 01, 2019 To: PREMIER FARNELL PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

We request you acknowledge receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If you require samples or additional data to support your evaluation, please request within 30 days.

The changes discussed within this PCN will not take effect any earlier than **90** days from the date of this notification, unless customer agreement has been reached on an earlier implementation of the change. This notification period is per TI's standard process.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice, contact your local Field Sales Representative or the PCN Team (<u>PCN ww admin team@list.ti.com</u>). For sample requests or sample related questions, contact your local Field Sales Representative.

PCN Team SC Business Services

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, these are the devices that you have purchased within the past twenty-four (24) months. The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
LM1876TF/NOPB	null
LM3886T/NOPB	null
LM3886TF/NOPB	null
LM4766T/NOPB	null
LM2876TF/NOPB	null

Technical details of this Product Change follow on the next page(s).

PCN Number: 201906				90627003.1				PCN Date: July 3			1, 2019	
Title: Transfer of select HV700 devices from GFAB to FFAB Wafer Fab site												
Customer	[.] Conta	ct:	PC	N Manage	er		Dept:		Qua	lity Se	ervices	
Proposed 1 st Ship Date:		Oct	Oct 1, 2019		Estimated Sample Availability:			Date provided at sample request.				
Change Ty								_				
	nbly Sit	е		Assemb				Assembly Materials				
Design						cification	0	\mathbb{H}		Mechanical Specification		
Test Site Wafer Bump Site				Packing/Shipping/Labeling Wafer Bump Material			y .	\mathbb{H}		Test Process Wafer Bump Process		
Wafer Fab Site				Wafer F						Wafer Fab Process		
	Part numbe			mber o	change							
				F	PCN I	Details						
Descriptio												
-						fer of select devices liste						
	Cı	urrent Fa	ıb Site	•			ľ	lev	/ Fab Sit	е		
Current Site	Current Fab Proce				afer neter	New Fa	ab	Process			Wafer Diameter	
GFAB		HV7	700) mm	FFAB			HV700		200 mm	
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Qualification Report

Approve Date 24-June-2019

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: LM3886T/NOPB
AC	Autoclave, 121C	96 Hours	3/231/0
ED	Electrical Characterization	rical Characterization Per Datasheet Parameters	
ELFR	Early Life Failure Rate, 125C	48 Hours	3/2400/0
HAST	Biased HAST, 130C/85%RH	96 Hours	3/231/0
HBM	ESD - HBM	3000 V	3/9/0
CDM	ESD - CDM	1000 V	3/9/0
HTOL	Life Test, 125C	1000 Hours	3/231/0
HTSL	High Temp. Storage Bake, 150C	1000 Hours	3/231/0
LU	Latch-up	(per JESD78)	3/18/0
TC	Temperature Cycle, -65/150C	500 Cycles	3231/0

- Qual Device LM3886T/NOPB is qualified at LEVEL1-260C

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle and HTSL as applicable.

- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours - The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Timp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
WW PCN Team	PCN ww admin team@list.ti.com